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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	51
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l072rzt6

Table 3. Functionalities depending on the operating power supply range

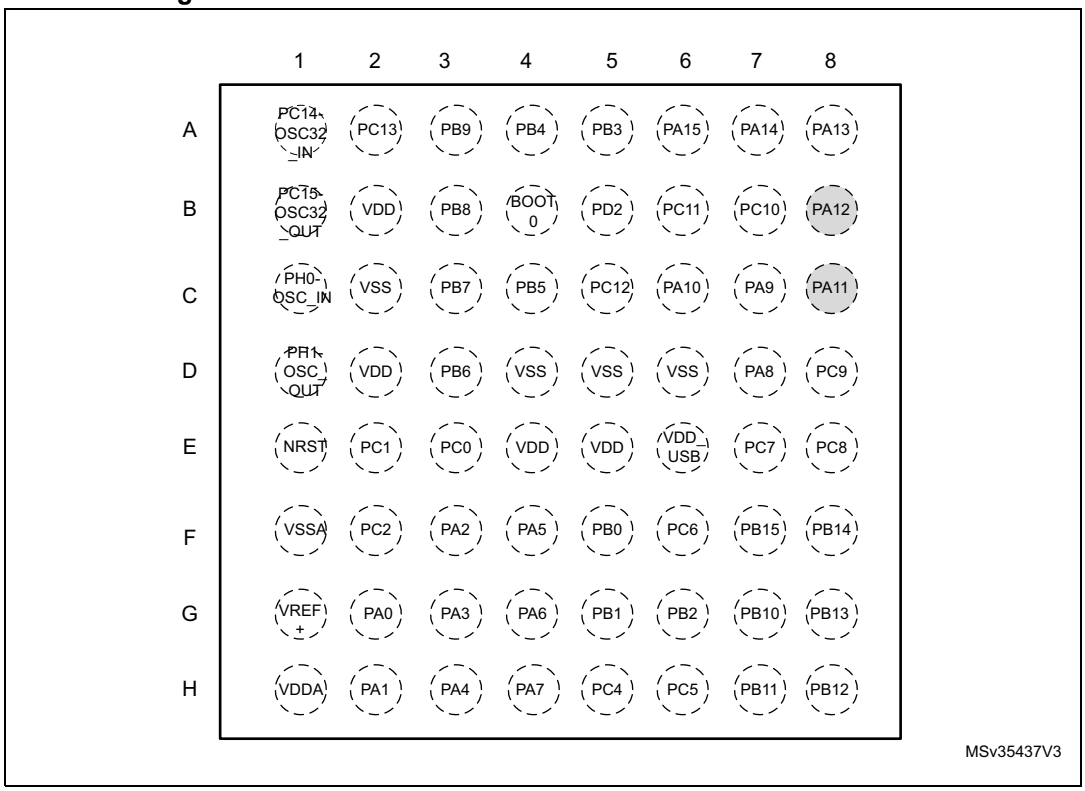
Operating power supply range	Functionalities depending on the operating power supply range			
	DAC and ADC operation	Dynamic voltage scaling range	I/O operation	USB
V_{DD} = 1.65 to 1.71 V	ADC only, conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance	Not functional
V_{DD} = 1.71 to 1.8 V(1)	ADC only, conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance	Functional(2)
V_{DD} = 1.8 to 2.0 V(1)	Conversion time up to 1.14 Msps	Range1, range 2 or range 3	Degraded speed performance	Functional(2)
V_{DD} = 2.0 to 2.4 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation	Functional(2)
V_{DD} = 2.4 to 3.6 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation	Functional(2)

1. CPU frequency changes from initial to final must respect "fcpu initial <4*fcpu final". It must also respect 5 µs delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2 MHz to 16 MHz, wait 5 µs, then switch from 16 MHz to 32 MHz.
2. To be USB compliant from the I/O voltage standpoint, the minimum V_{DD_USB} is 3.0 V.

Table 4. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
32 kHz to 4.2 MHz (0ws)	Range 3

Figure 6. STM32L072xx UFBGA64/TFBGA64 ballout - 5x 5 mm



1. The above figure shows the package top view.
2. I/O pin supplied by VDD_USB.

Table 16. STM32L072xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[1]	LQFP48	LQFP64	UFBGA64/TFBGA64	WLCSP49	LQFP100	UFBG100						
-	-	-	-	-	-	20	K1	VREF-	S		-	-	-
-	-	-	-	G1	E6	21	L1	VREF+	S		-	-	-
5	5	9	13	H1	F7	22	M1	VDDA	S		-	-	-
6	6	10	14	G2	E5	23	L2	PA0	I/O	TTa	-	TIM2_CH1, TSC_G1_IO1, USART2_CTS, TIM2_ETR, USART4_TX, COMP1_OUT	COMP1_INM, ADC_IN0, RTC_TAMP2/WKUP1
7	7	11	15	H2	E4	24	M2	PA1	I/O	FT	-	EVENTOUT, TIM2_CH2, TSC_G1_IO2, USART2_RTS, TIM21_ETR, USART4_RX	COMP1_INP, ADC_IN1
8	8	12	16	F3	F6	25	K3	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, TSC_G1_IO3, USART2_TX, LPUART1_TX, COMP2_OUT	COMP2_INM, ADC_IN2
9	9	13	17	G3	G7	26	L3	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, TSC_G1_IO4, USART2_RX, LPUART1_RX	COMP2_INP, ADC_IN3
-	-	-	18	C2	-	27	D3	VSS	S	-	-	-	-
-	-	-	19	D2	-	28	H3	VDD	S	-	-	-	-
10	10	14	20	H3	F5	29	M3	PA4	I/O	TC	(2)	SPI1_NSS, TSC_G2_IO1, USART2_CK, TIM22_ETR	COMP1_INM, COMP2_INM, ADC_IN4, DAC_OUT1
11	11	15	21	F4	G6	30	K4	PA5	I/O	TC	-	SPI1_SCK, TIM2_ETR, TSC_G2_IO2, TIM2_CH1	COMP1_INM, COMP2_INM, ADC_IN5, DAC_OUT2

Table 16. STM32L072xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[1]	LQFP48	LQFP64	UFBGA64/TFBGA64	WLCSP49	LQFP100	UFBG100						
12	12	16	22	G4	G5	31	L4	PA6	I/O	FT	-	SPI1_MISO, TIM3_CH1, TSC_G2_IO3, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
13	13	17	23	H4	F4	32	M4	PA7	I/O	FT	-	SPI1_MOSI, TIM3_CH2, TSC_G2_IO4, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
-	-	-	24	H5	-	33	K5	PC4	I/O	FT	-	EVENTOUT, LPUART1_TX	ADC_IN14
-	-	-	25	H6	-	34	L5	PC5	I/O	FT	-	LPUART1_RX, TSC_G3_IO1	ADC_IN15
14	14	18	26	F5	G4	35	M5	PB0	I/O	FT	-	EVENTOUT, TIM3_CH3, TSC_G3_IO2	ADC_IN8, VREF_OUT
15	15	19	27	G5	D3	36	M6	PB1	I/O	FT	-	TIM3_CH4, TSC_G3_IO3, LPUART1_RTS	ADC_IN9, VREF_OUT
-	-	20	28	G6	E3	37	L6	PB2	I/O	FT	-	LPTIM1_OUT, TSC_G3_IO4, I2C3_SMBA	-
-	-	-	-	-	-	38	M7	PE7	I/O	FT	-	USART5_CK/USART5_RTS_DE	-
-	-	-	-	-	-	39	L7	PE8	I/O	FT	-	USART4_TX	-
-	-	-	-	-	-	40	M8	PE9	I/O	FT	-	TIM2_CH1, TIM2_ETR, USART4_RX	-
-	-	-	-	-	-	41	L8	PE10	I/O	FT	-	TIM2_CH2, USART5_TX	-
-	-	-	-	-	-	42	M9	PE11	I/O	FT	-	TIM2_CH3, USART5_RX	-
-	-	-	-	-	-	43	L9	PE12	I/O	FT	-	TIM2_CH4, SPI1_NSS	-
-	-	-	-	-	-	44	M10	PE13	I/O	FT	-	SPI1_SCK	-
-	-	-	-	-	-	45	M11	PE14	I/O	FT	-	SPI1_MISO	-

Table 16. STM32L072xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[1]	LQFP48	LQFP64	UFBGA64/TFBGA64	WLCSP49	LQFP100	UFBG100						
-	24	36	48	E6	A1	75	G11	VDD_USB	S		-	-	-
24	25	37	49	A7	B2	76	A10	PA14	I/O	FT	-	SWCLK, USART2_TX, LPUART1_TX	-
25	-	38	50	A6	A2	77	A9	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1, USART4_RTS_DE	-
-	-	-	51	B7	-	78	B11	PC10	I/O	FT	-	LPUART1_TX, USART4_TX	-
-	-	-	52	B6	-	79	C10	PC11	I/O	FT	-	LPUART1_RX, USART4_RX	-
-	-	-	53	C5	-	80	B10	PC12	I/O	FT	-	USART5_TX, USART4_CK	-
-	-	-	-	-	-	81	C9	PD0	I/O	FT	-	TIM21_CH1, SPI2_NSS/I2S2_WS	-
-	-	-	-	-	-	82	B9	PD1	I/O	FT	-	SPI2_SCK/I2S2_CK	-
-	-	-	54	B5	-	83	C8	PD2	I/O	FT	-	LPUART1_RTS_DE, TIM3_ETR, USART5_RX	-
-	-	-	-	-	-	84	B8	PD3	I/O	FT	-	USART2_CTS, SPI2_MISO/I2S2_MCK	-
-	-	-	-	-	-	85	B7	PD4	I/O	FT	-	USART2_RTS_DE, SPI2_MOSI/I2S2_SD	-
-	-	-	-	-	-	86	A6	PD5	I/O	FT	-	USART2_TX	-
-	-	-	-	-	-	87	B6	PD6	I/O	FT	-	USART2_RX	-
-	-	-	-	-	-	88	A5	PD7	I/O	FT	-	USART2_CK, TIM21_CH2	-
26	-	39	55	A5	A3	89	A8	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, TSC_G5I_O1, EVENTOUT, USART1__RTS_DE, USART5_TX	COMP2_INM

Table 24. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD} (2)	Total current into sum of all V_{DD} power lines (source)(1)	105	mA
ΣI_{VSS} (2)	Total current out of sum of all V_{SS} ground lines (sink)(1)	105	
ΣI_{VDD_USB}	Total current into V_{DD_USB} power lines (source)	25	
$I_{VDD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)	100	
$I_{VSS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
I_{IO}	Output current sunk by any I/O and control pin except FTf pins	16	
	Output current sunk by FTf pins	22	
	Output current sourced by any I/O and control pin	-16	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins except PA11 and PA12(2)	90	
	Total output current sunk by PA11 and PA12	25	
	Total output current sourced by sum of all IOs and control pins(2)	-90	
$I_{INJ(PIN)}$	Injected current on FT, FFf, RST and B pins	-5/+0(3)	
	Injected current on TC pin	± 5(4)	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(5)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 23* for maximum allowed input voltage values.
4. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 23: Voltage characteristics* for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 25. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 30. Current consumption in Run mode, code with data processing running from Flash memory

Symbol	Parameter	Condition		f_{HCLK} (MHz)	Typ	Max(1)	Unit
I_{DD} (Run from Flash memory)	Supply current in Run mode code executed from Flash memory	$f_{HSE} = f_{HCLK}$ up to 16MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range3, Vcore=1.2 V VOS[1:0]=11	1	190	250	µA
				2	345	380	
				4	650	670	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	0,8	0,86	mA
				8	1,55	1,7	
				16	2,95	3,1	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	1,9	2,1	
				16	3,55	3,8	
				32	6,65	7,2	
		MSI clock source	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	39	130	µA
				0,524	115	210	
				4,2	700	770	
		HSI clock source (16MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	2,9	3,2	mA
			Range1, Vcore=1.8 V VOS[1:0]=01	32	7,15	7,4	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 31. Current consumption in Run mode vs code type, code with data processing running from Flash memory

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from Flash memory)	Supply current in Run mode, code executed from Flash memory	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL on)(1)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	650	µA
				CoreMark		655	
				Fibonacci		485	
				while(1)		385	
				while(1), 1WS, prefetch off		375	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	6,65	mA
				CoreMark		6,9	
				Fibonacci		6,75	
				while(1)		5,8	
				while(1), prefetch off		5,5	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on

Table 40. Peripheral current consumption in Run or Sleep mode(1)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C				Unit
		Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	Low-power sleep and run	
APB1	CRS	2.5	2	2	2	µA/MHz (f_{HCLK})
	DAC1/2	4	3.5	3	2.5	
	I2C1	11	9.5	7.5	9	
	I2C3	11	9	7	9	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	
	SPI2	9	4.5	3.5	4	
	USB	8.5	4.5	4	4.5	
	USART2	14.5	12	9.5	11	
	USART4	5	4	3	5	
	USART5	5	4	3	5	
	TIM2	10.5	8.5	7	9	
	TIM3	12	10	8	11	
	TIM6	3.5	3	2.5	2	
	TIM7	3.5	3	2.5	2	
	WWDG	3	2	2	2	

6.3.7 Internal clock source characteristics

The parameters given in *Table 47* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 26*.

High-speed internal 16 MHz (HSI16) RC oscillator

Table 47. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI16 user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
$ACC_{HSI16}^{(2)}$	Accuracy of the factory-calibrated HSI16 oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = − 40 to 125 °C	-5.45	-	3.25	%
$t_{SU(HSI16)}^{(2)}$	HSI16 oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI16)}^{(2)}$	HSI16 oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Figure 25. HSI16 minimum and maximum value versus temperature

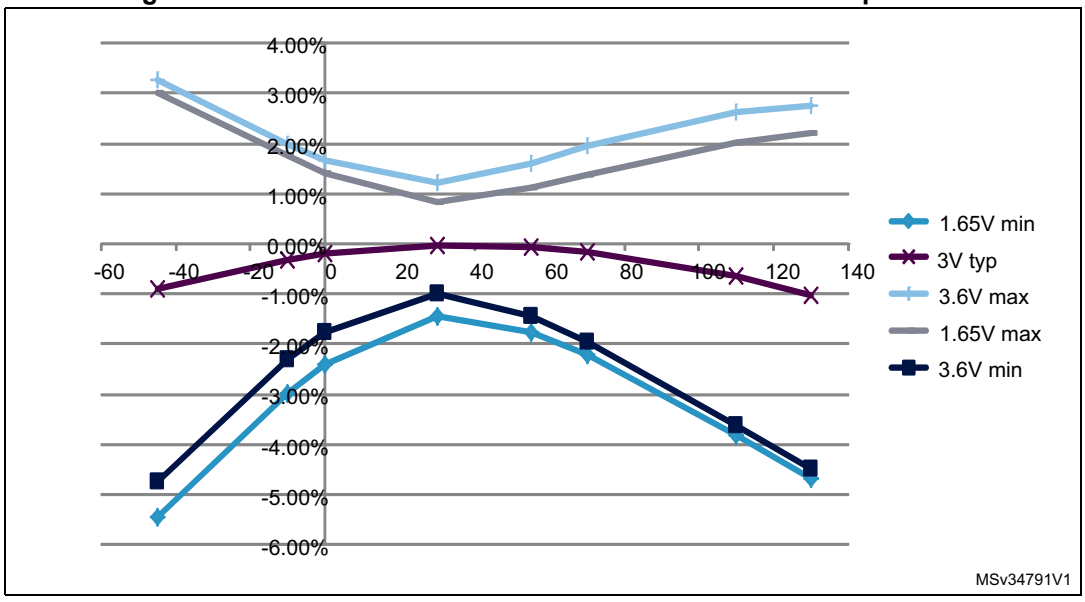


Figure 26. V_{IH}/V_{IL} versus VDD (CMOS I/Os)

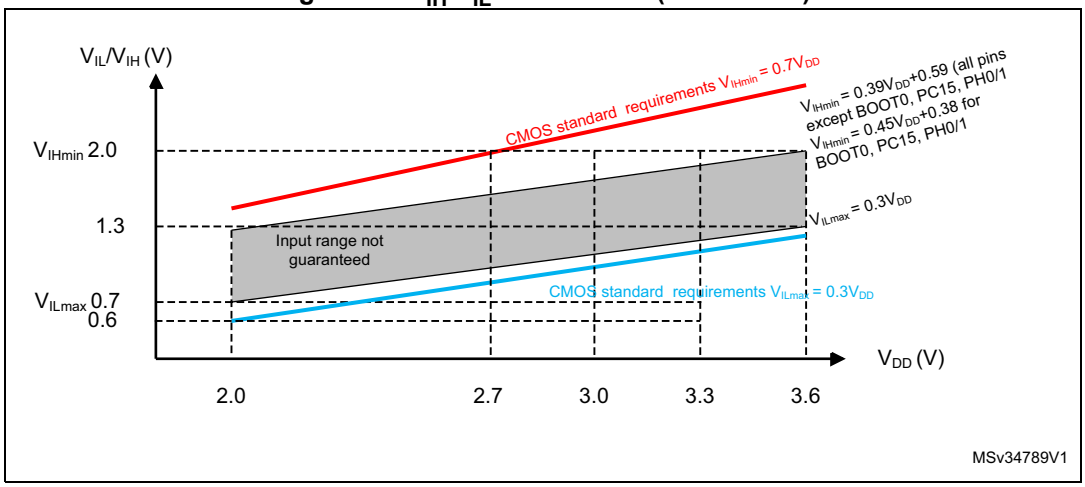
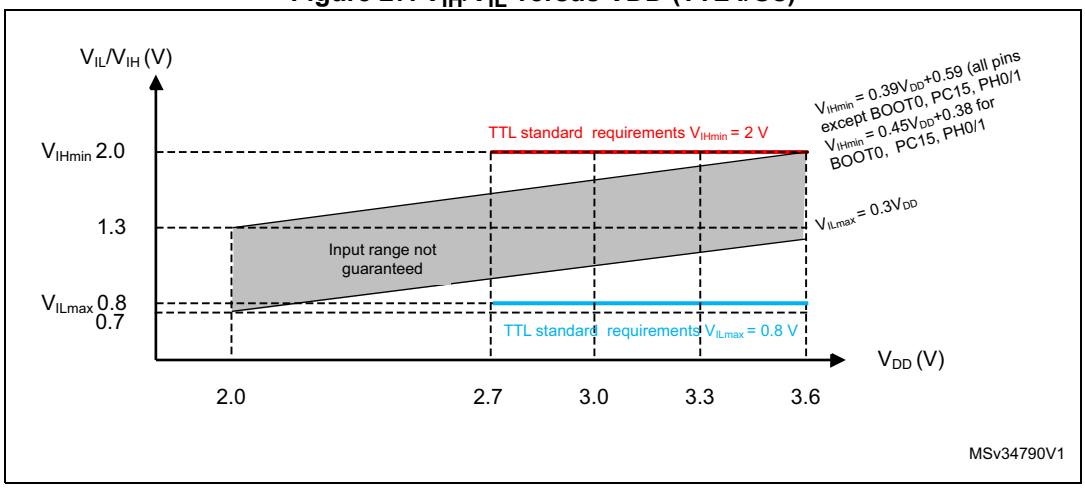


Figure 27. V_{IH}/V_{IL} versus VDD (TTL I/Os)



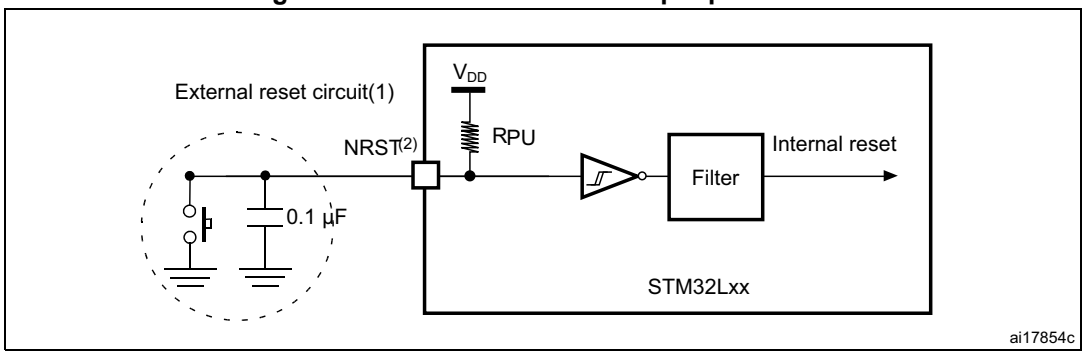
Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±15 mA with the non-standard V_{OL}/V_{OH} specifications given in *Table 61*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating $I_{VDD(\Sigma)}$ (see *Table 24*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating $I_{VSS(\Sigma)}$ (see *Table 24*).

Figure 29. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 63*. Otherwise the reset will not be taken into account by the device.

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 64* are derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in *Table 26: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 64. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for ADC on	Fast channel	1.65	-	3.6	V
		Standard channel	1.75(1)	-	3.6	
V_{REF+}	Positive reference voltage	-	1.65		V_{DDA}	V
V_{REF-}	Negative reference voltage	-	-	0	-	
$I_{DDA\ (ADC)}$	Current consumption of the ADC on V_{DDA} and V_{REF+}	1.14 Msps	-	200	-	µA
		10 ksps	-	40	-	
	Current consumption of the ADC on V_{DD}(2)	1.14 Msps	-	70	-	
		10 ksps	-	1	-	
f_{ADC}	ADC clock frequency	Voltage scaling Range 1	0.14	-	16	MHz
		Voltage scaling Range 2	0.14	-	8	
		Voltage scaling Range 3	0.14	-	4	
f_S(3)	Sampling rate	12-bit resolution	0.01	-	1.14	MHz
f_{TRIG}(3)	External trigger frequency	f_{ADC} = 16 MHz, 12-bit resolution	-	-	941	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range	-	0	-	V_{REF+}	V
R_{AIN}(3)	External input impedance	See *Equation 1* and *Table 65* for details	-	-	50	kΩ
R_{ADC}(3)(4)	Sampling switch resistance	-	-	-	1	kΩ

Table 64. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{ADC} (3)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL} (3)(5)	Calibration time	f_{ADC} = 16 MHz	5.2			µs
		-	83			$1/f_{ADC}$
$W_{LATENCY}$ (6)	ADC_DR register write latency	ADC clock = HSI16	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr} (3)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2$ = 16 MHz	0.266			µs
		$f_{ADC} = f_{PCLK}/2$	8.5			$1/f_{PCLK}$
		$f_{ADC} = f_{PCLK}/4$ = 8 MHz	0.516			µs
		$f_{ADC} = f_{PCLK}/4$	16.5			$1/f_{PCLK}$
		$f_{ADC} = f_{HSI16}$ = 16 MHz	0.252	-	0.260	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	$f_{ADC} = f_{HSI16}$	-	1	-	$1/f_{HSI16}$
t_S (3)	Sampling time	f_{ADC} = 16 MHz	0.093	-	10.03	µs
		-	1.5	-	160.5	$1/f_{ADC}$
t_{UP_LDO} (3)(5)	Internal LDO power-up time	-	-	-	10	µs
t_{STAB} (3)(5)	ADC stabilization time	-	14			$1/f_{ADC}$
t_{ConV} (3)	Total conversion time (including sampling time)	f_{ADC} = 16 MHz, 12-bit resolution	0.875	-	10.81	µs
		12-bit resolution	14 to 173 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

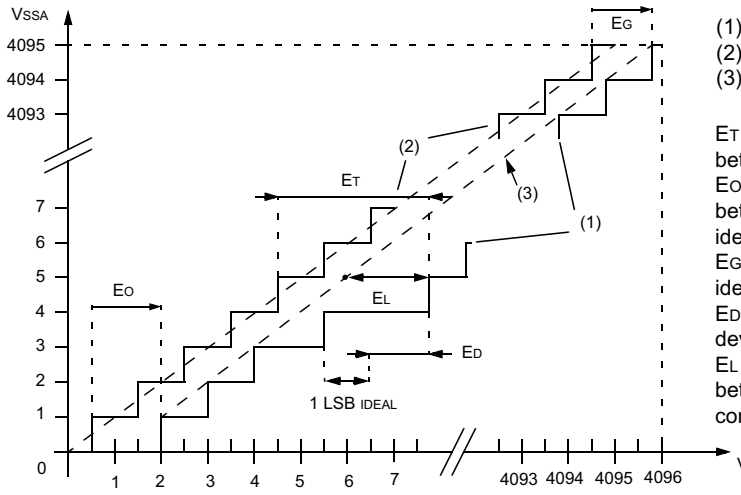
1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 65: RAIN max for fADC = 16 MHz*.
2. A current consumption proportional to the APB clock frequency has to be added (see *Table 40: Peripheral current consumption in Run or Sleep mode*).
3. Guaranteed by design.
4. Standard channels have an extra protection resistance which depends on supply voltage. Refer to *Table 65: RAIN max for fADC = 16 MHz*.
5. This parameter only includes the ADC timing. It does not take into account register access latency.
6. This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

Table 66. ADC accuracy(1)(2)(3) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ET	Total unadjusted error	1.65 V < V_{REF+} <V_{DDA} < 3.6 V, range 1/2/3	-	2	5	LSB
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	
EL	Integral linearity error		-	1.5	3	
ED	Differential linearity error		-	1	2	
ENOB	Effective number of bits		10.0	11.0	-	bits
SINAD	Signal-to-noise distortion		62	69	-	dB
SNR	Signal-to-noise ratio		61	69	-	
THD	Total harmonic distortion		-	-85	-65	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.12* does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.

Figure 30. ADC accuracy characteristics



(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

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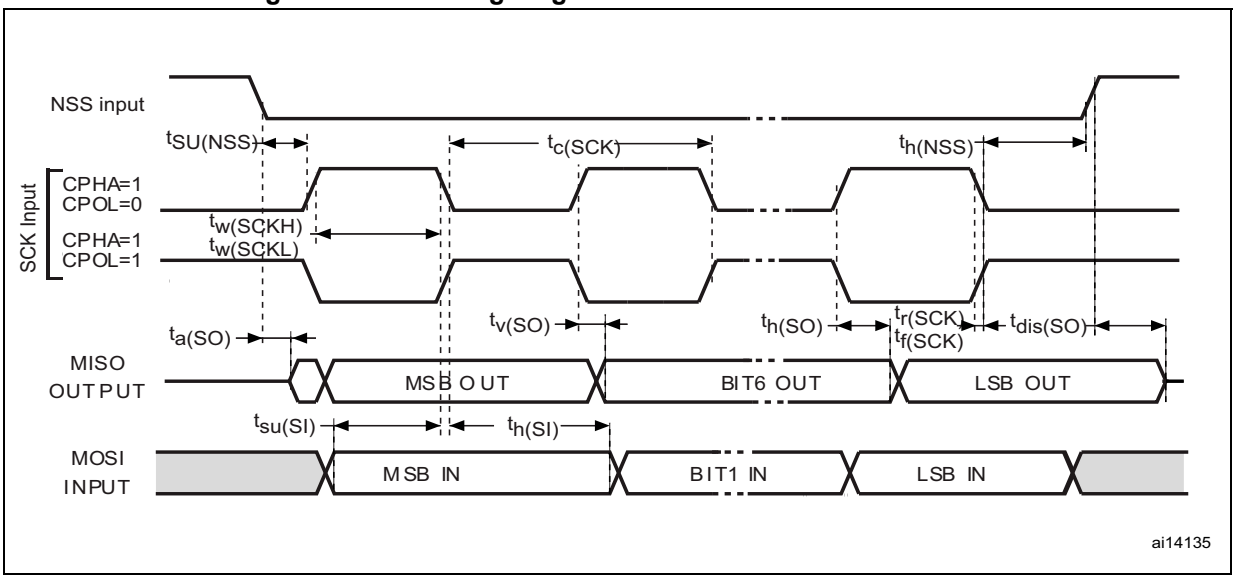
Table 67. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
dOffset/dT(2)	Offset error temperature coefficient (code 0x800)	V_{DDA} = 3.3V V_{REF+}= 3.0 V T_A = 0 to 50 °C DAC output buffer off	-20	-10	0	µV/°C
		V_{DDA} = 3.3V V_{REF+}= 3.0 V T_A = 0 to 50 °C DAC output buffer on	0	20	50	
Gain(2)	Gain error(8)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer on	-	+0.1 / -0.2%	+0.2 / -0.5%	%
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer off	-	+0 / -0.2%	+0 / -0.4%	
dGain/dT(2)	Gain error temperature coefficient	V_{DDA} = 3.3V V_{REF+}= 3.0 V T_A = 0 to 50 °C DAC output buffer off	-10	-2	0	µV/°C
		V_{DDA} = 3.3V V_{REF+}= 3.0 V T_A = 0 to 50 °C DAC output buffer on	-40	-8	0	
TUE(2)	Total unadjusted error	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ DAC output buffer on	-	12	30	LSB
		No R_{LOAD}, $C_L \leq$ 50 pF DAC output buffer off	-	8	12	
$t_{SETTLING}$	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	7	12	µs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	-	1	Msps
t_{WAKEUP}	Wakeup time from off state (setting the ENx bit in the DAC Control register)(9)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	9	15	µs
PSRR+	V_{DDA} supply rejection ratio (static DC measurement)	$C_L \leq$ 50 pF, $R_L \geq$ 5 kΩ	-	-60	-35	dB

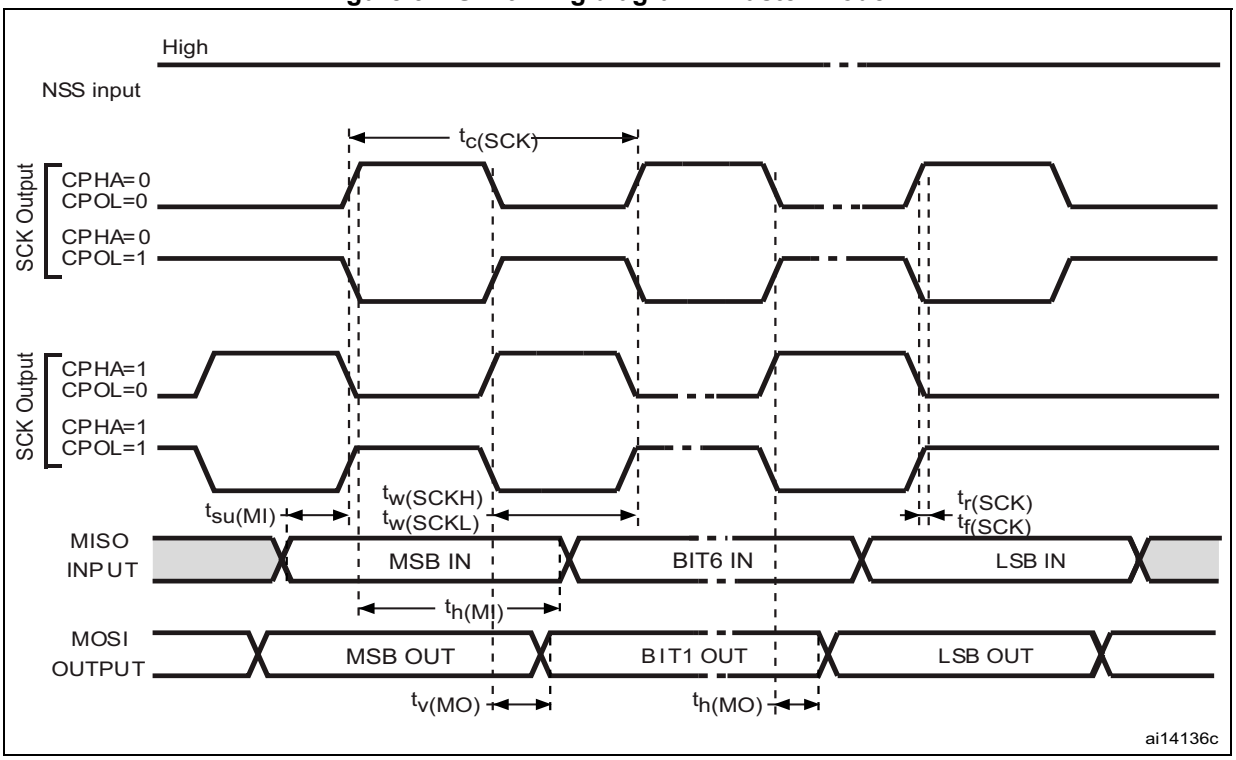
1. Guaranteed by characterization results.
2. Guaranteed by design, not tested in production.
3. Connected between DAC_OUT and V_{SSA}.
4. Difference between two consecutive codes - 1 LSB.
5. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.

Figure 36. SPI timing diagram - slave mode and CPHA = 1(1)



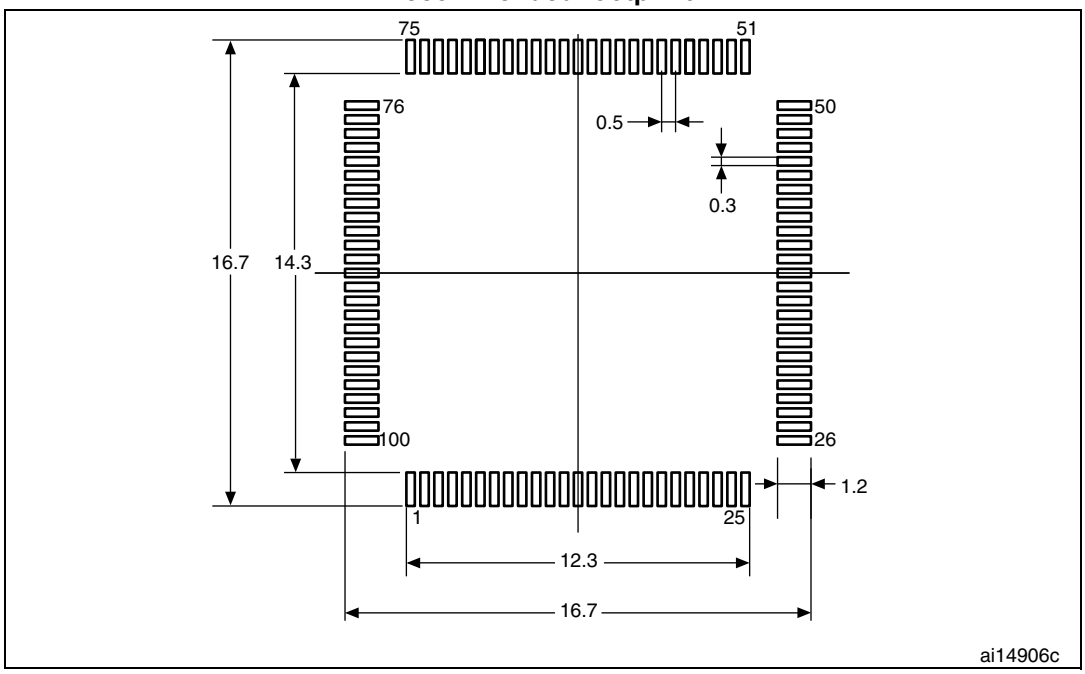
1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 37. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

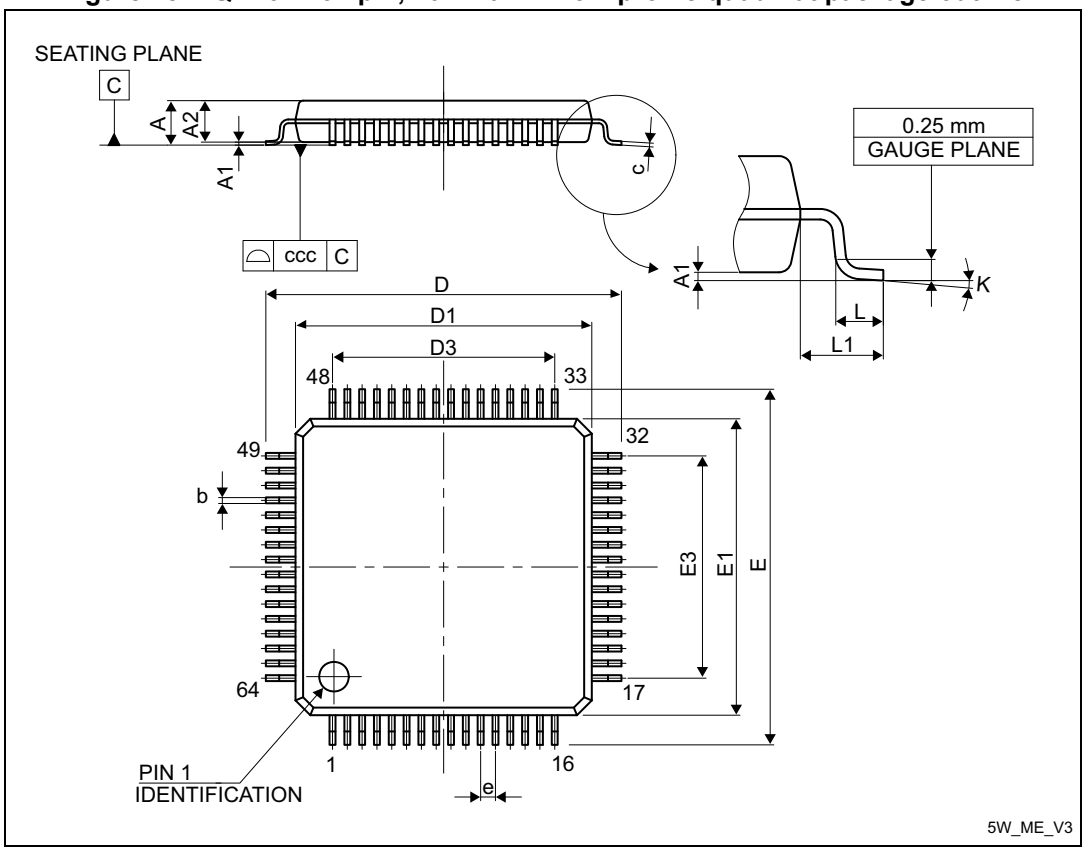
Figure 42. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

7.3 LQFP64 package information

Figure 45. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



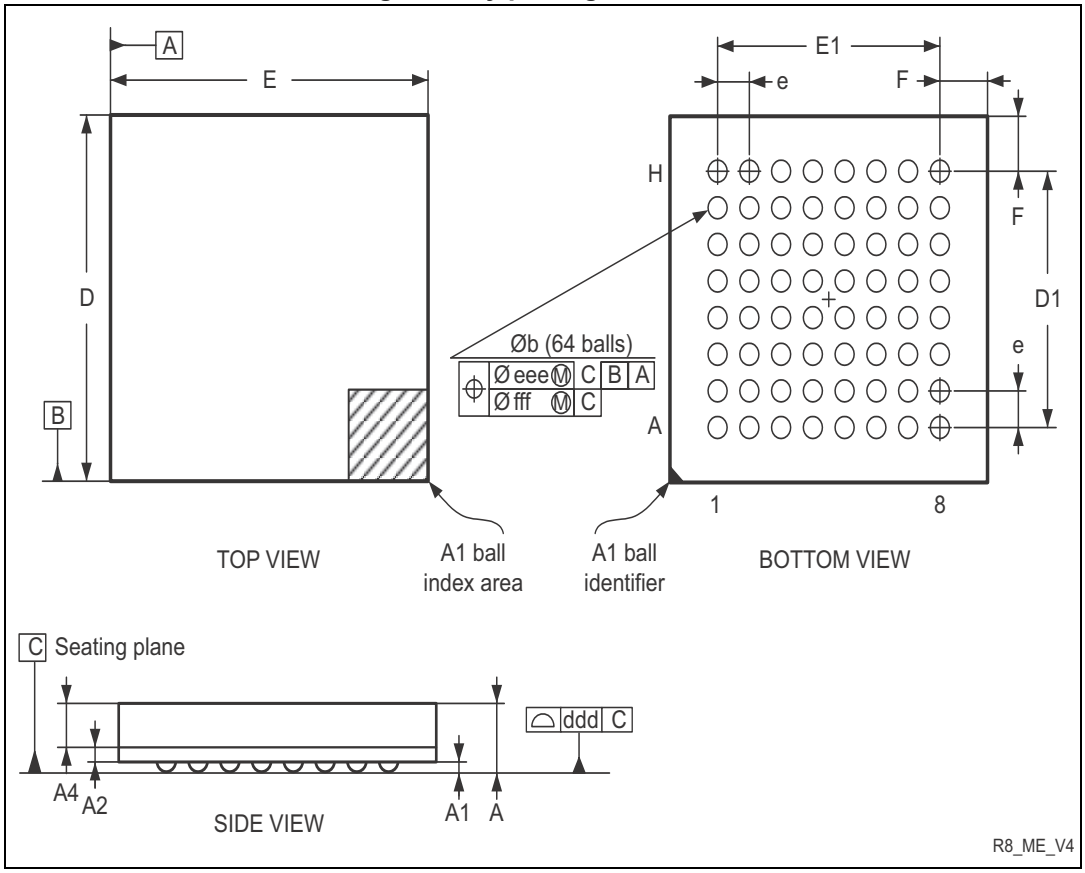
1. Drawing is not to scale.

Table 85. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

7.5 TFBGA64 package information

Figure 51. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 88. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-

Table 88. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
e	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 52. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball ,grid array recommended footprint

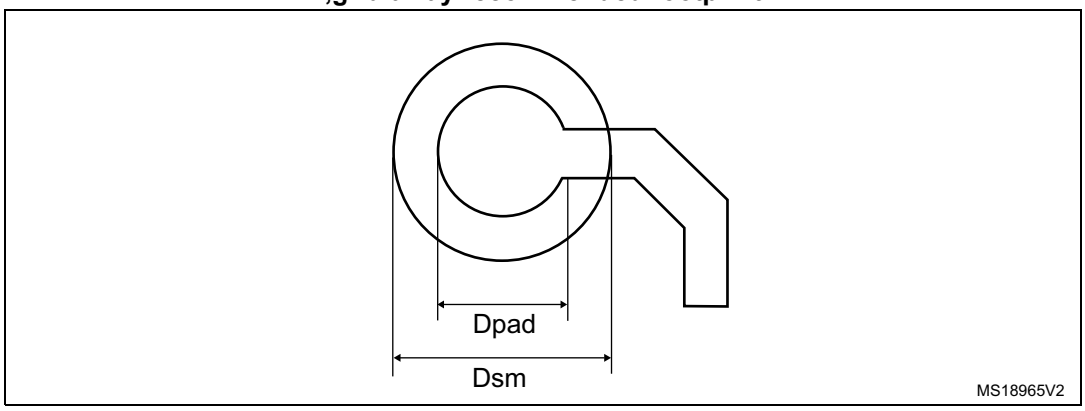


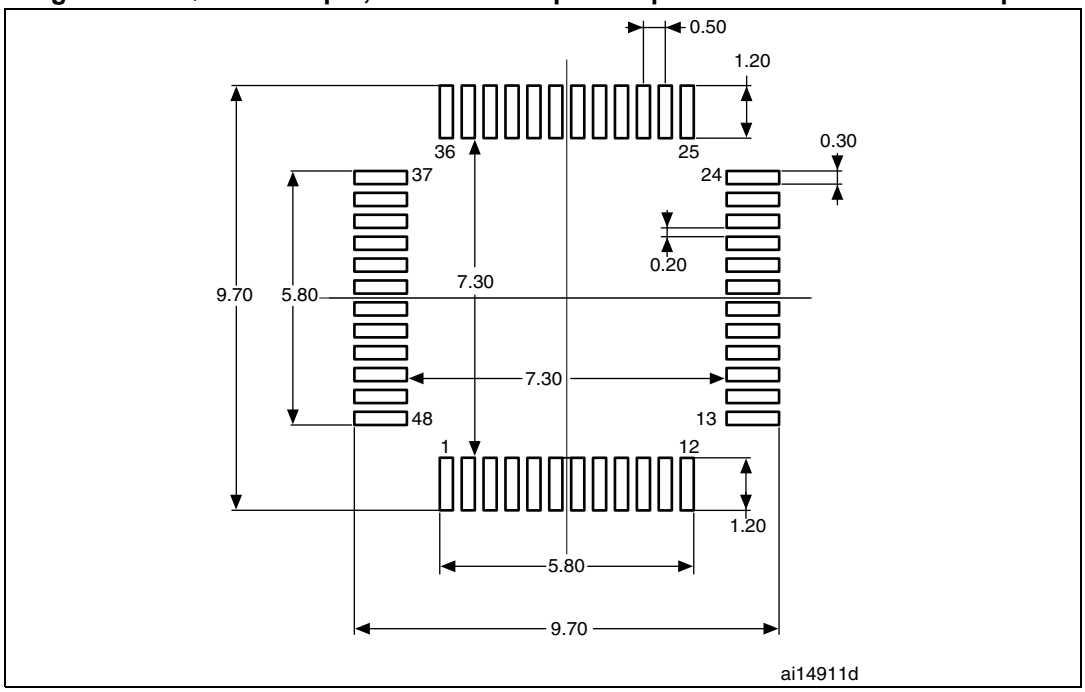
Table 89. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.27 mm
Dsm	0.35 mm typ. (depends on the soldermask registration tolerance)
Solder paste	0.27 mm aperture diameter.

Note: Non solder mask defined (NSMD) pads are recommended.

4 to 6 mils solder paste screen printing process.

Figure 58. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.